Application No. 09/762, Paper Dated: August 11, 2003

In Reply to USPTO Correspondence of April 10, 2003

Attorney Docket No. 702-010166

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning at page 2, line 32 with the following rewritten paragraph:

- -- A second aspect of the present invention provides a process for providing the device of the present invention, wherein gas plasma is deposited under the following conditions:
 - a.) a discharge power of up to 5000 W, for example up to 500 W;
 - b.) an exposure duration of up to 1000 s, for example up to 100 s;
 - c.) a plasma gas flow of up to 10000 cm³/min, for example up to 100
 - d.) a pressure of up to 1 bar, for example up to 0.001-50 mbar; and
- e.) a frequency covering DC, AC, RF, and the MW ranges, for example a frequency between 2-60 Mhz,

wherein the discharge power is pulsed to the plasma, the pulse discharges being separated by up to 100 s. --

cm³/min;